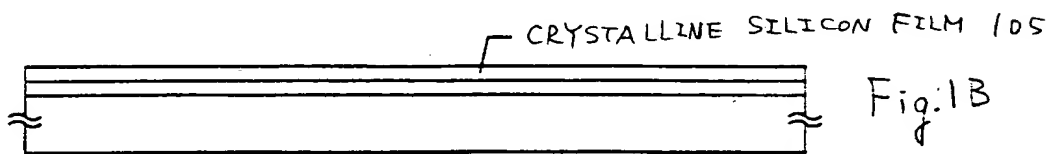
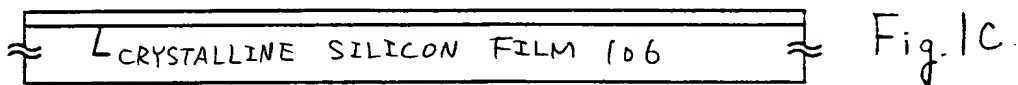


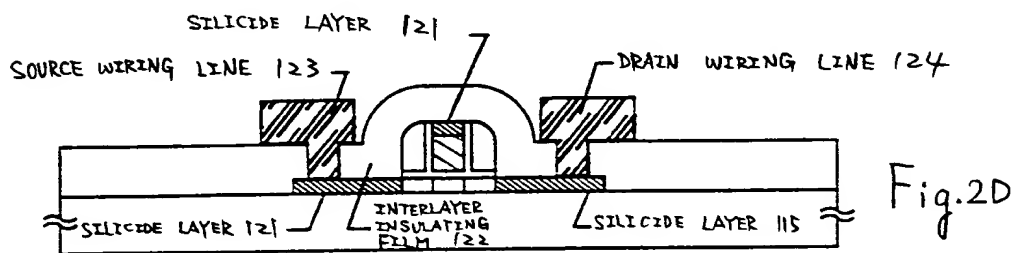
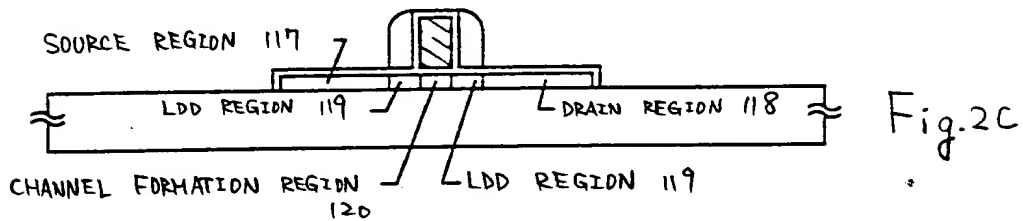
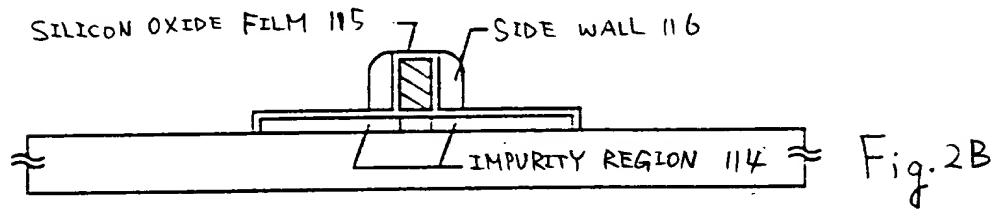
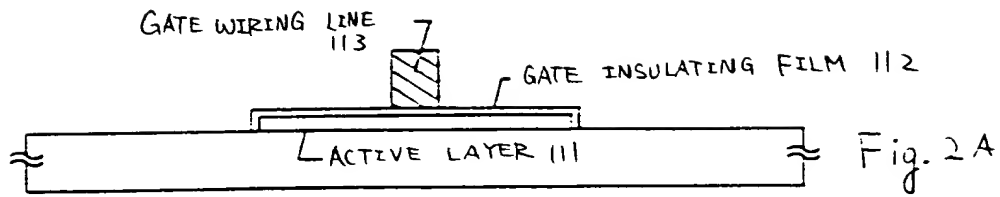
LASER CRYSTALLIZATION STEP



THERMAL TREATMENT STEP IN REDUCING ATMOSPHERE



27



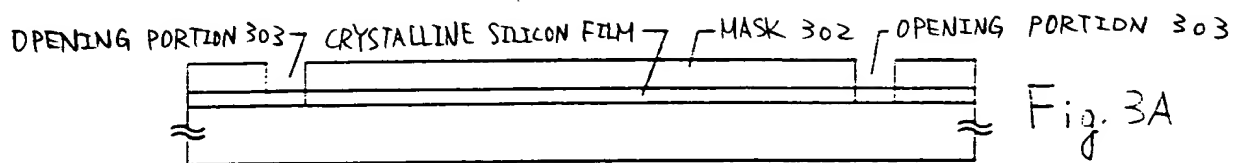


Fig. 3A

ADDING STEP OF PHOSPHORUS

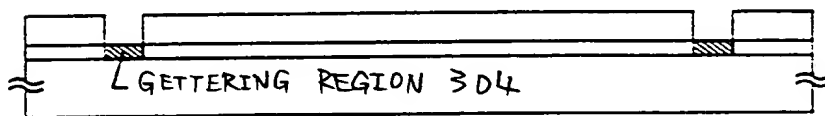


Fig. 3B

GETTERING STEP

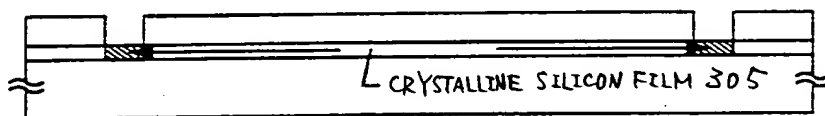


Fig. 3C

HEAT TREATMENT STEP IN REDUCING ATMOSPHERE

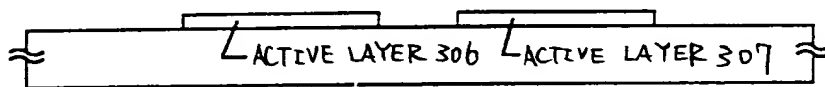


Fig. 3D

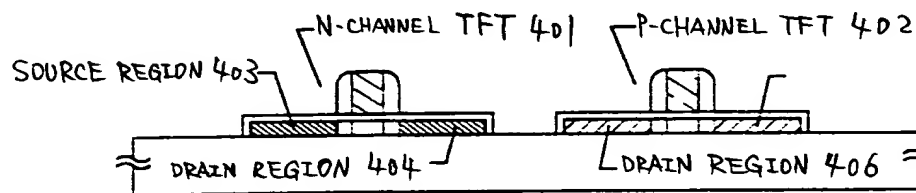


Fig. 4A

GETTERING STEP

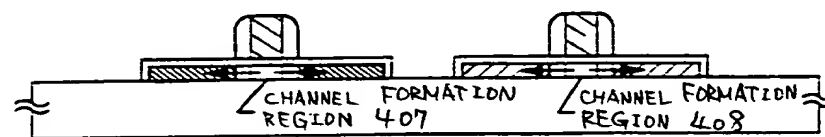


Fig. 4B

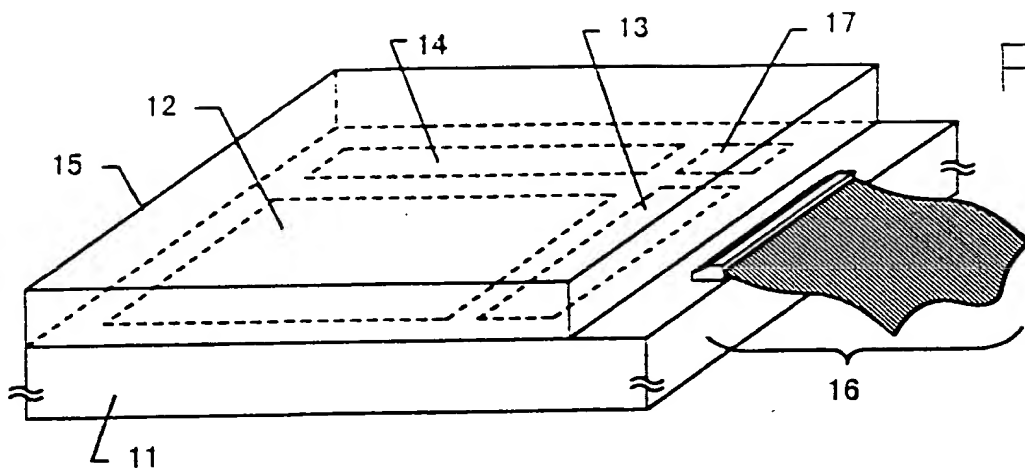


Fig. 5A

- 11: SUBSTRATE HAVING INSULATING SURFACE 12: PIXEL MATRIX CIRCUIT  
 13: SOURCE DRIVER CIRCUIT 14: GATE DRIVER CIRCUIT  
 15: OPPOSITE SUBSTRATE 16: FPC  
 17: SIGNAL PROCESSING CIRCUIT

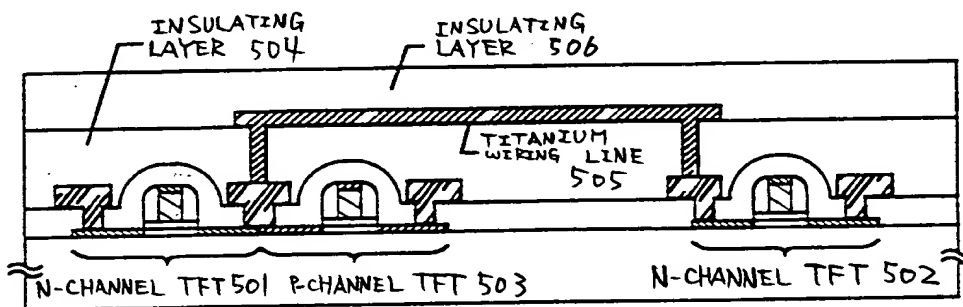


Fig. 5B

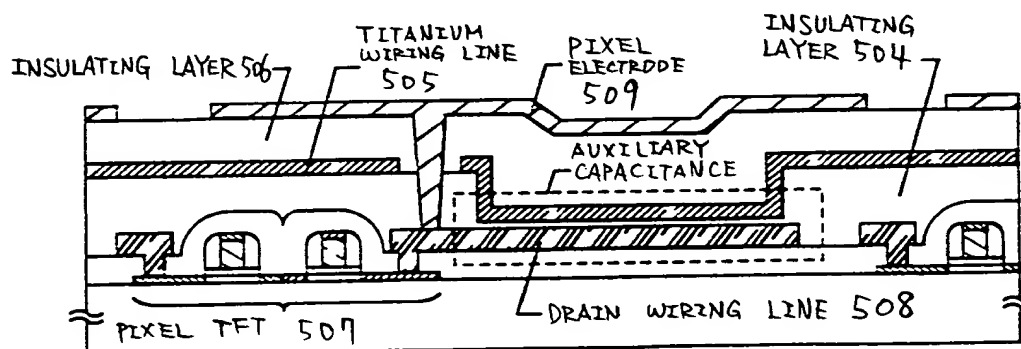


Fig. 5C

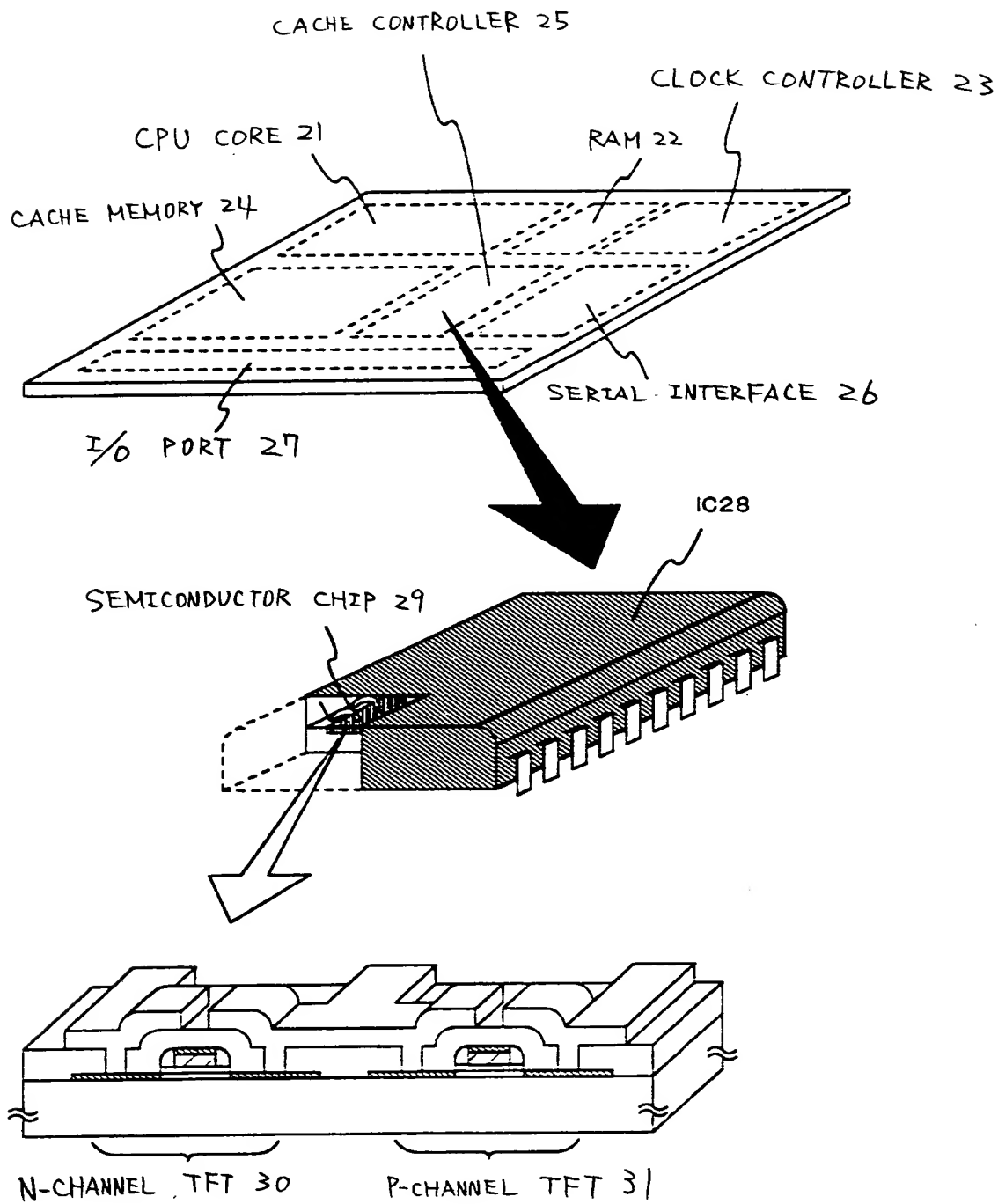
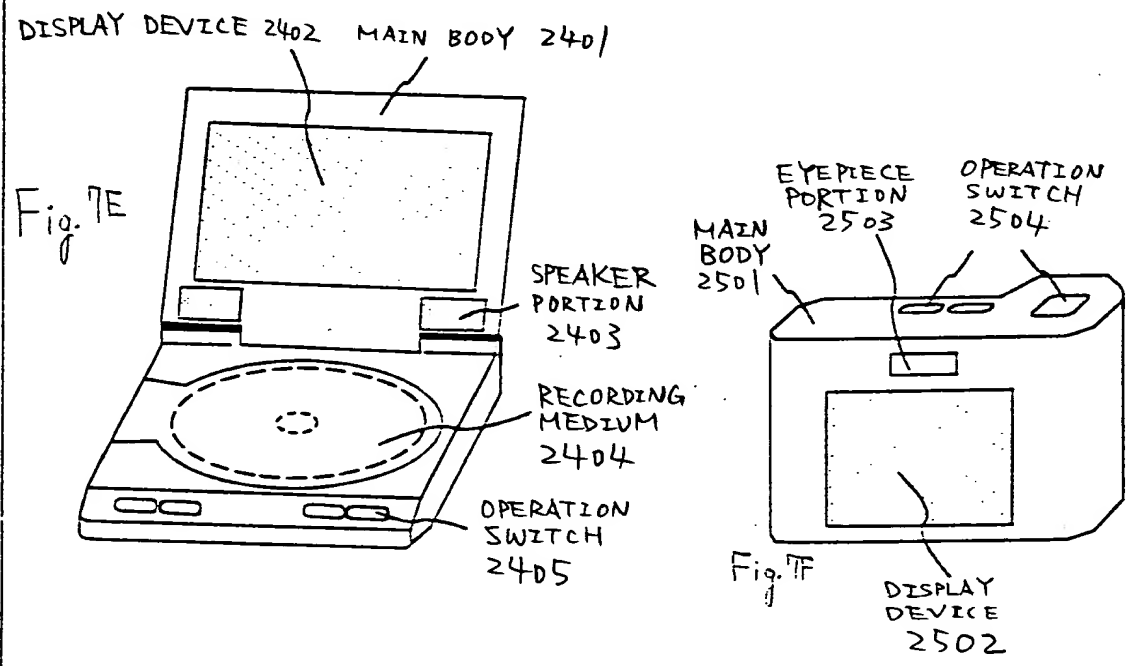
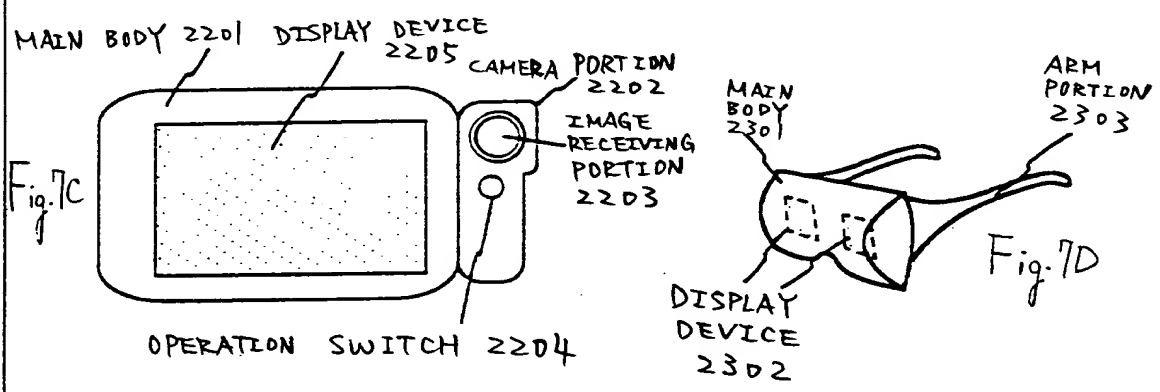
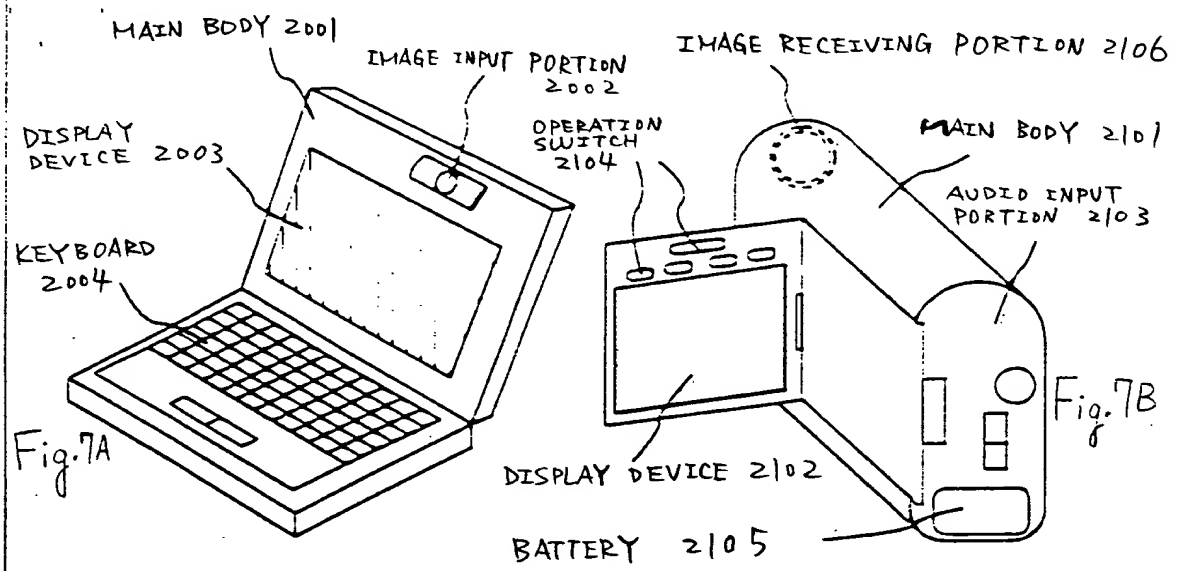


Fig. 6



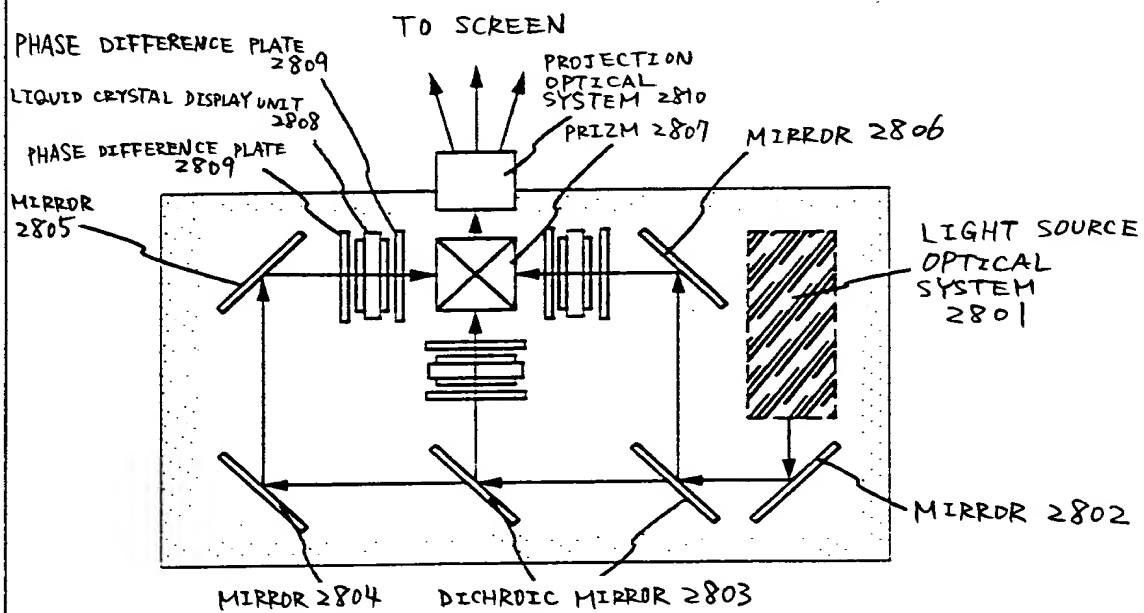
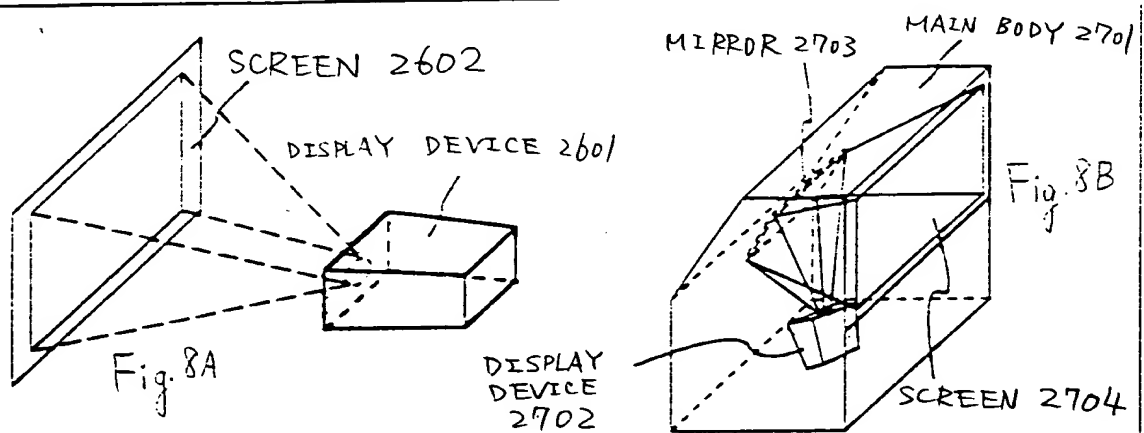


Fig. 8C DISPLAY DEVICE (THREE-PLATE TYPE)

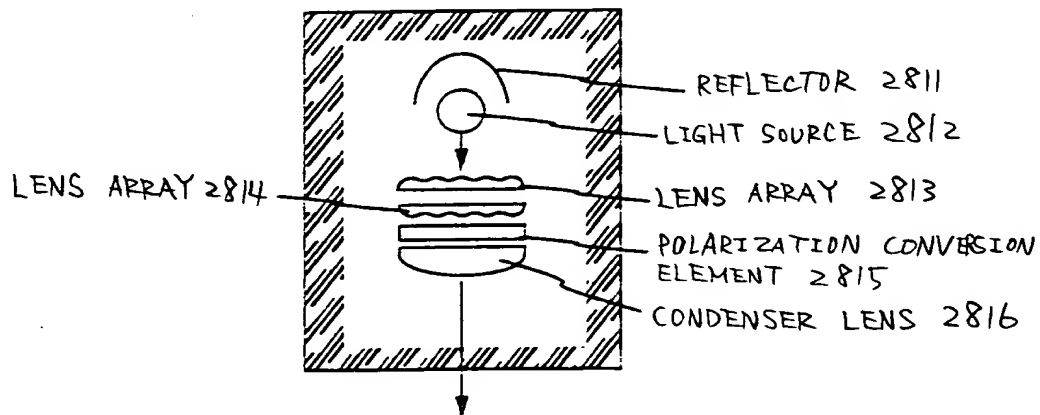


Fig. 8D LIGHT SOURCE OPTICAL SYSTEM

DIFFRACTION  
SPOT 801

303

Fig. 9A

CENTER POINT OF BEAM IRRADIATION AREA 802

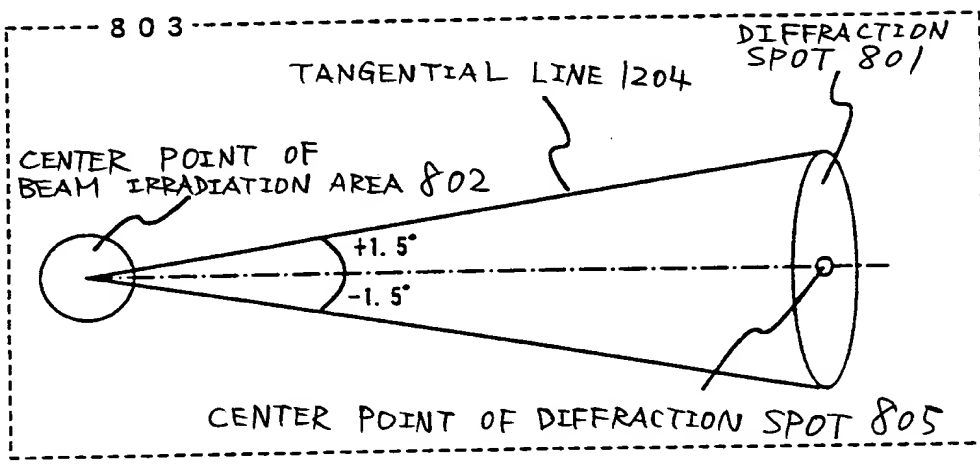


Fig. 9B



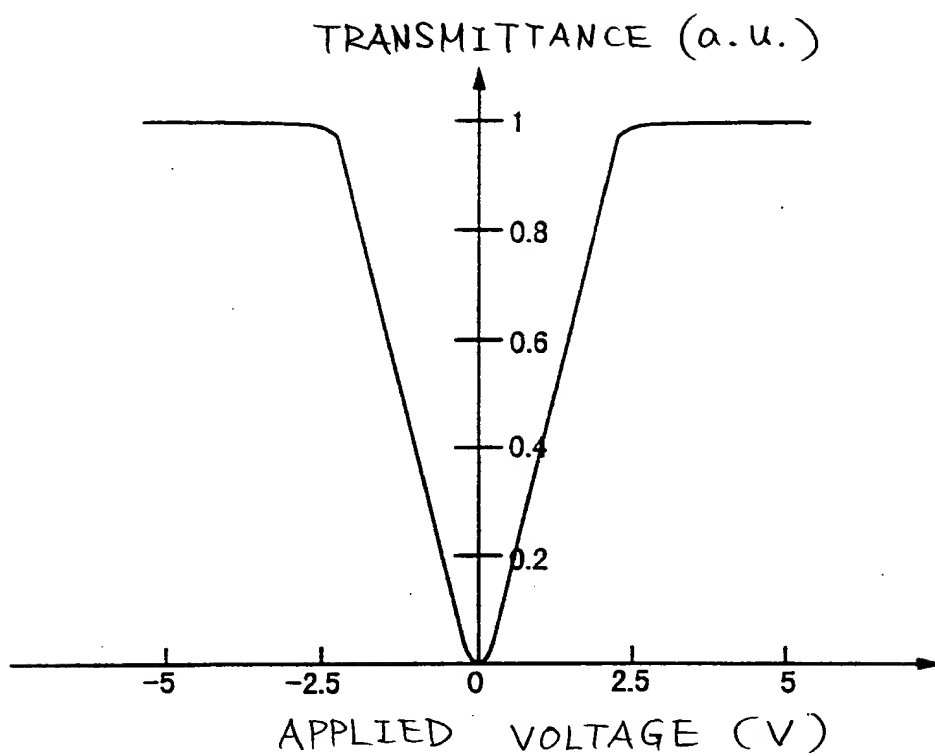


Fig.10

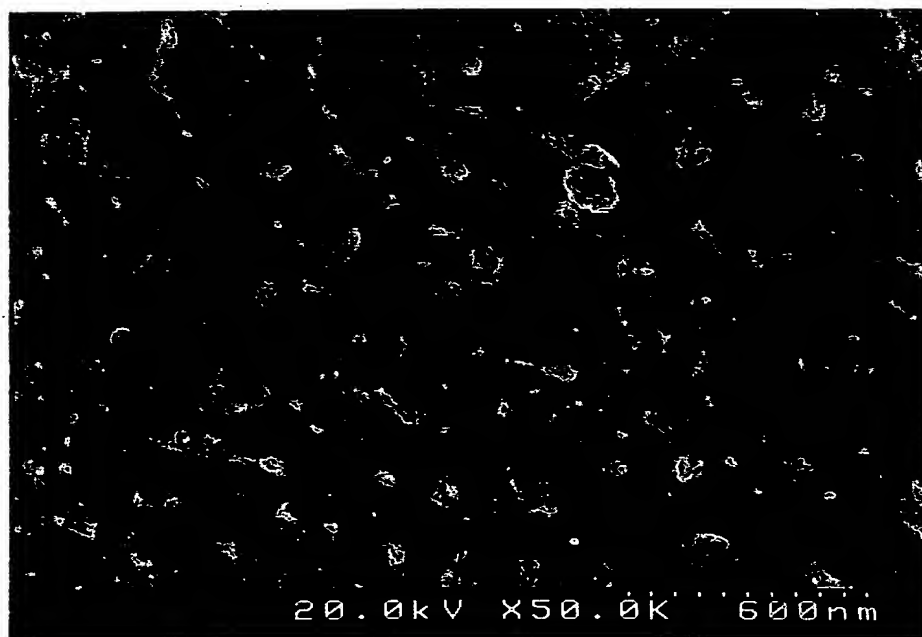


Fig.11

BEFORE HIGH TEMPERATURE ANNEALING

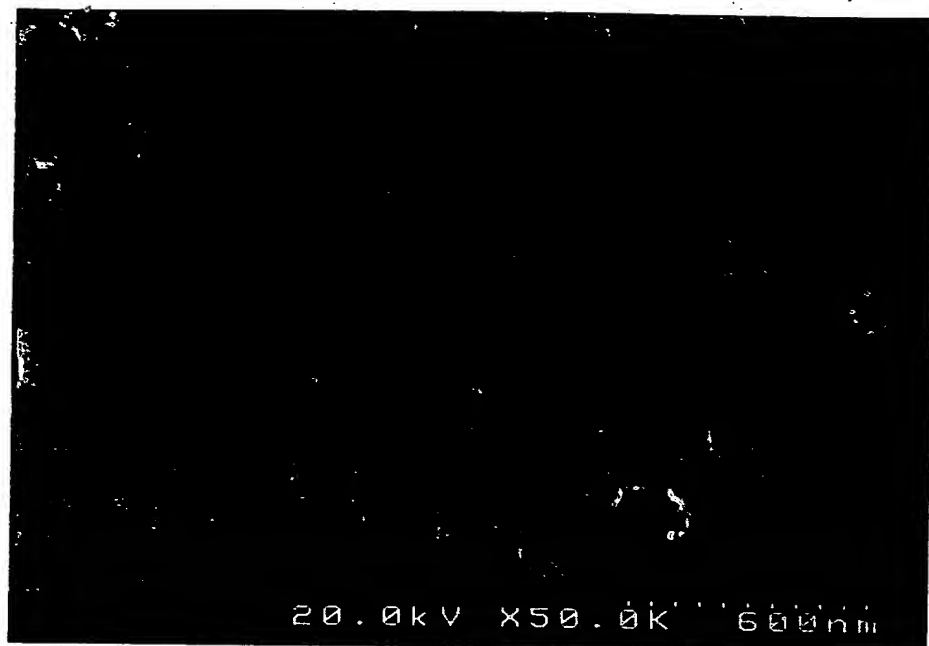


Fig.12

AFTER HIGH TEMPERATURE ANNEALING

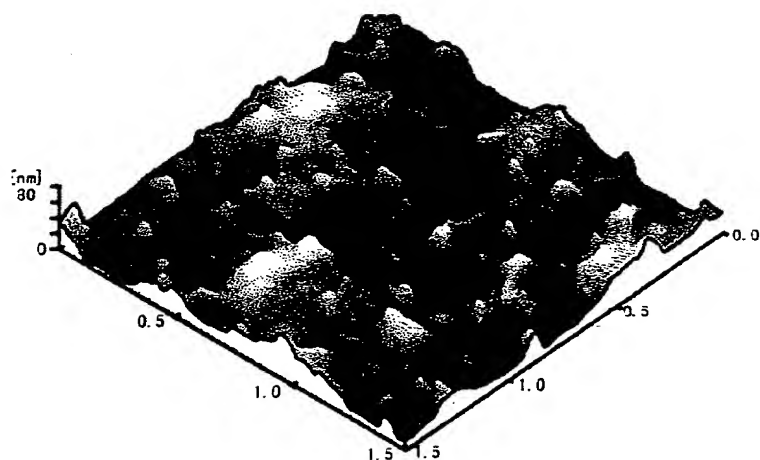
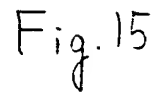
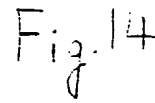


Fig.13

BEFORE HIGH TEMPERATURE ANNEALING



BEFORE HIGH TEMPERATURE ANNEALING

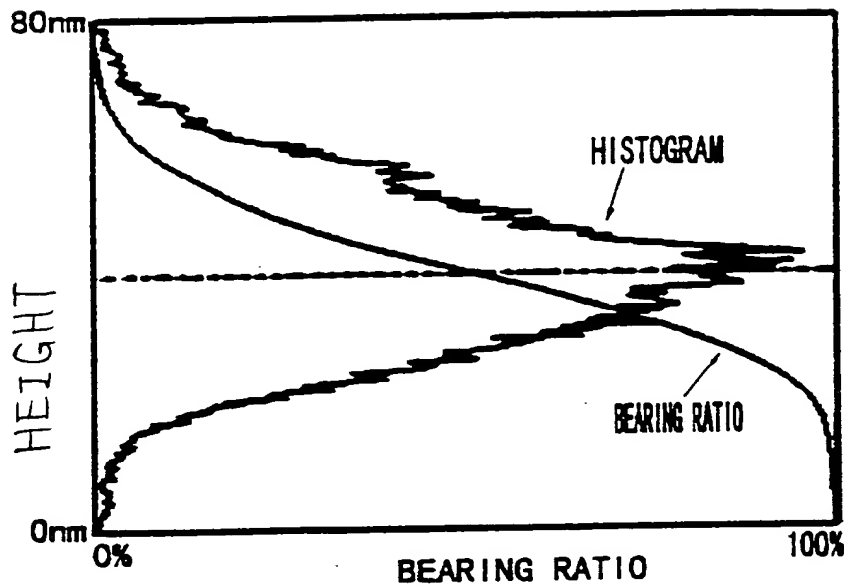


Fig.16

AFTER HIGH TEMPERATURE ANNEALING

OBSERVATION REGION	BEFORE HIGH TEMPERATURE ANNEALING	AFTER HIGH TEMPERATURE ANNEALING
1	13.623	40.925
2	20.027	51.126
3	20.629	59.364
4	21.798	48.539
5	16.666	55.341
6	15.097	46.510
7	13.120	57.655
8	14.035	51.120
9	12.599	54.416
10	20.699	36.945
MINIMUM VALUE (%)	12.60	36.95
MAXIMUM VALUE (%)	21.80	59.36
AVERAGE VALUE (%)	16.83	50.19
STANDARD DEVIATION $\sigma$	3.61	7.18

Fig.17

BEARING RATIO AT  $2\sigma$  (P-V VALUE) (%)